



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel and P-Channel Silicon MOSFETs

FW907 — General-Purpose Switching Device Applications

Features

- ON-resistance Nch: $R_{DS(on)1}=13m\Omega(typ.)$, Pch: $R_{DS(on)1}=20m\Omega(typ.)$
- 4V drive
- N-channel MOSFET + P-channel MOSFET

Specifications

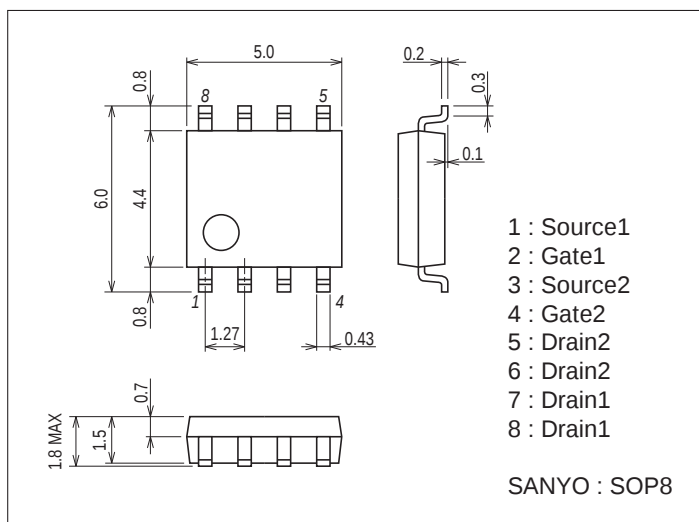
Absolute Maximum Ratings at $T_a=25^\circ C$

Parameter	Symbol	Conditions	N-channel	P-channel	Unit
Drain-to-Source Voltage	V_{DS}		30	-30	V
Gate-to-Source Voltage	V_{GS}		± 20	± 20	V
Drain Current (DC)	I_D		10	-8	A
Drain Current ($PW \leq 10s$)	I_D	Duty cycle $\leq 1\%$	11.5	-9	A
Drain Current ($PW \leq 100ms$)	I_D	Duty cycle $\leq 1\%$	24	-19	A
Drain Current ($PW \leq 10\mu s$)	I_{DP}	Duty cycle $\leq 1\%$	52	-52	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate ($2000mm^2 \times 0.8mm$) 1unit, $PW \leq 10s$	2.3		W
Total Dissipation	P_T	When mounted on ceramic substrate ($2000mm^2 \times 0.8mm$), $PW \leq 10s$	2.5		W
Channel Temperature	T_{ch}		150		$^\circ C$
Storage Temperature	T_{stg}		-55 to +150		$^\circ C$

Package Dimensions

unit : mm (typ)

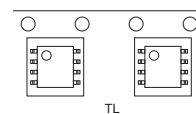
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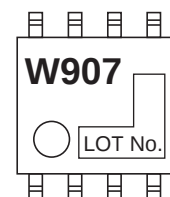
Product & Package Information

- Package : SOP8
- JEITA, JEDEC : SC-87, SOT96
- Minimum Packing Quantity : 1,000 pcs./reel

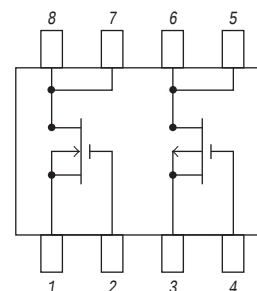
Packing Type : TL



Marking



Electrical Connection



SANYO Semiconductor Co., Ltd.

<http://semicon.sanyo.com/en/network>

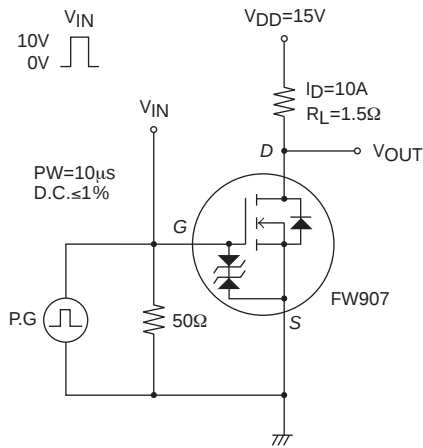
FW907

Electrical Characteristics at Ta=25°C

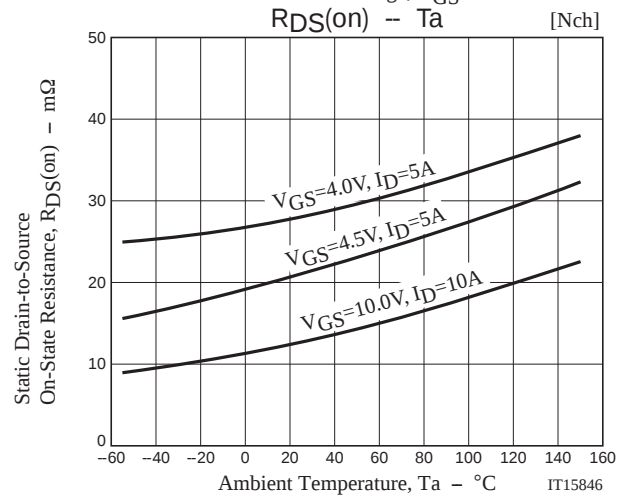
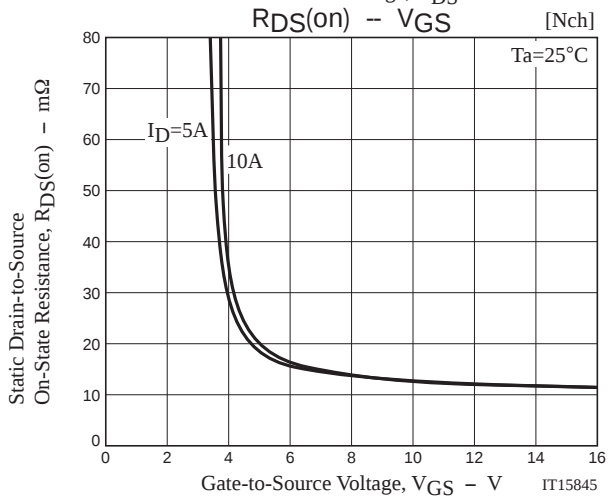
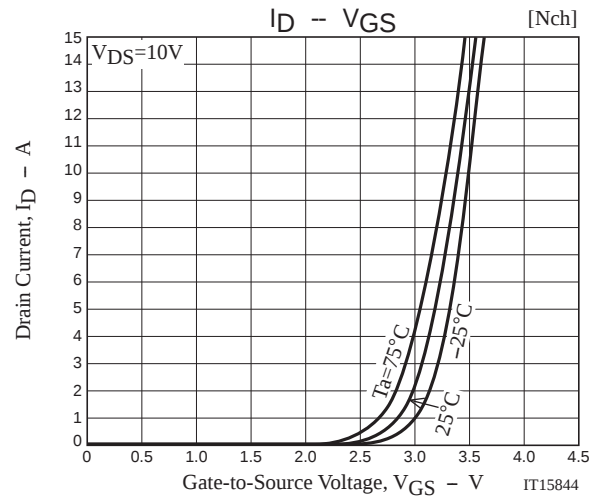
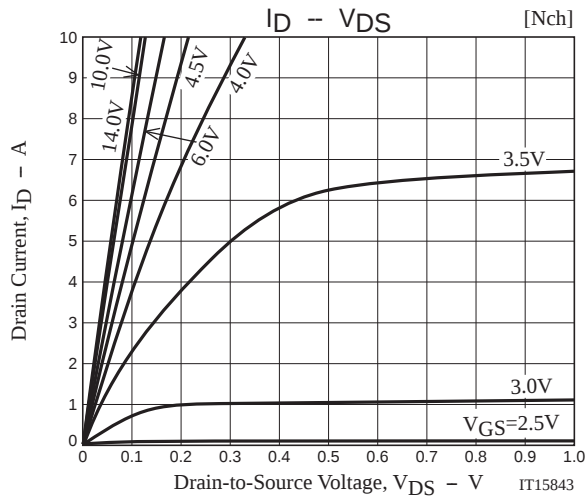
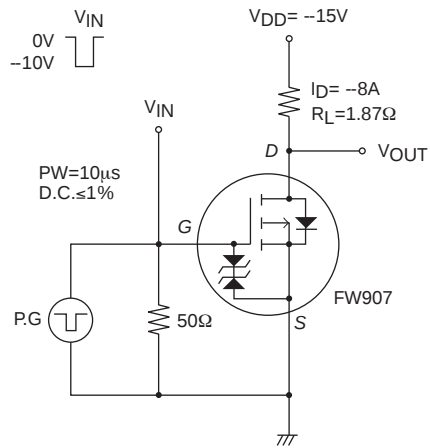
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	VDS=30V, VGS=0V			1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±16V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=10A		5.2		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=10A, VGS=10V		13	17	mΩ
	RDS(on)2	ID=5A, VGS=4.5V		21	30	mΩ
	RDS(on)3	ID=5A, VGS=4V		27	38	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		1000		pF
Output Capacitance	Coss	VDS=10V, f=1MHz		170		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		100		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		12		ns
Rise Time	tr	See specified Test Circuit.		75		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		57		ns
Fall Time	tf	See specified Test Circuit.		44		ns
Total Gate Charge	Qg	VDS=15V, VGS=10V, ID=10A		17		nC
Gate-to-Source Charge	Qgs	VDS=15V, VGS=10V, ID=10A		3.6		nC
Gate-to-Drain “Miller” Charge	Qgd	VDS=15V, VGS=10V, ID=10A		3.0		nC
Diode Forward Voltage	VSD	IS=10A, VGS=0V		0.85	1.2	V
[P-channel]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-30			V
Zero-Gate Voltage Drain Current	IDSS	VDS=-30V, VGS=0V			-1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±16V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=-10V, ID=-1mA	-1.2		-2.6	V
Forward Transfer Admittance	yfs	VDS=-10V, ID=-8A		10		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-8A, VGS=-10V		20	26	mΩ
	RDS(on)2	ID=-4A, VGS=-4.5V		32	45	mΩ
	RDS(on)3	ID=-4A, VGS=-4V		36	51	mΩ
Input Capacitance	Ciss	VDS=-10V, f=1MHz		875		pF
Output Capacitance	Coss	VDS=-10V, f=1MHz		200		pF
Reverse Transfer Capacitance	Crss	VDS=-10V, f=1MHz		150		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		8.1		ns
Rise Time	tr	See specified Test Circuit.		73		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		84		ns
Fall Time	tf	See specified Test Circuit.		74		ns
Total Gate Charge	Qg	VDS=-15V, VGS=-10V, ID=-8A		18		nC
Gate-to-Source Charge	Qgs	VDS=-15V, VGS=-10V, ID=-8A		2.1		nC
Gate-to-Drain “Miller” Charge	Qgd	VDS=-15V, VGS=-10V, ID=-8A		4.7		nC
Diode Forward Voltage	VSD	IS=-8A, VGS=0V		-0.82	-1.2	V

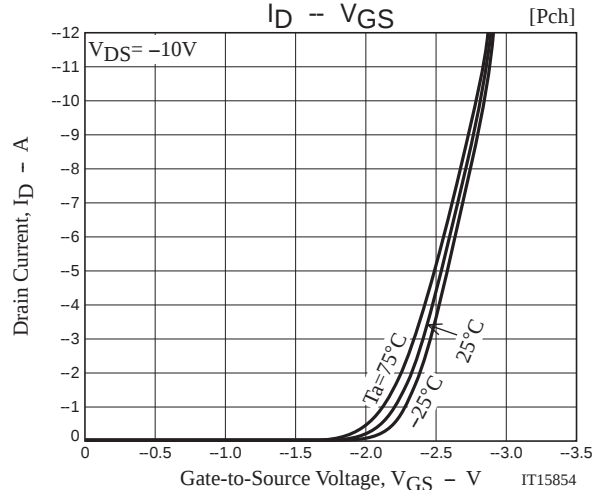
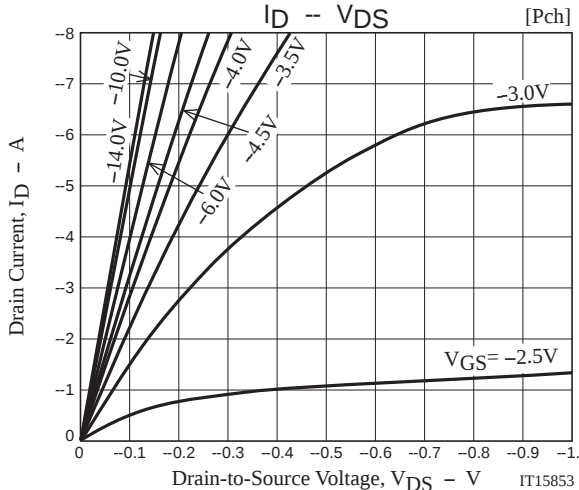
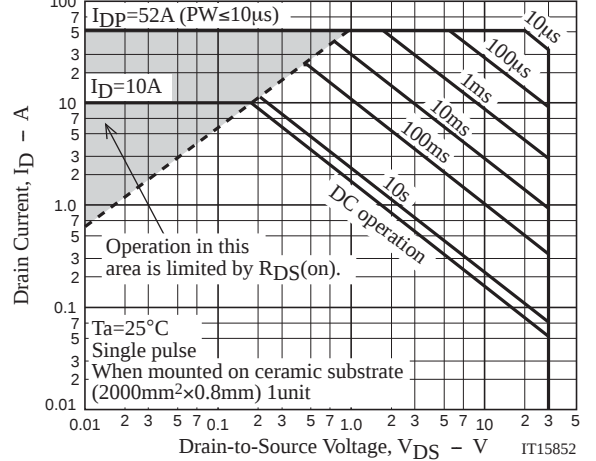
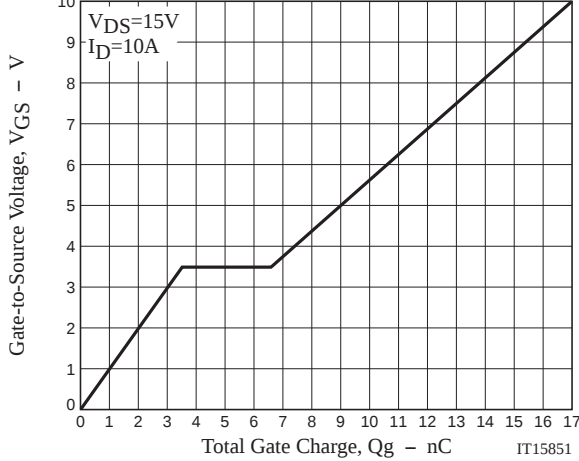
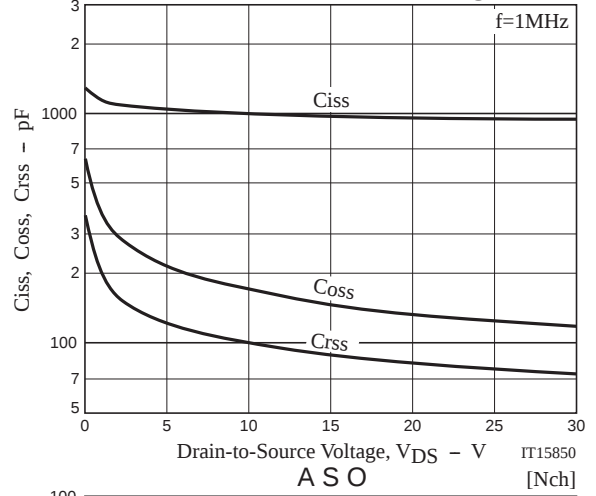
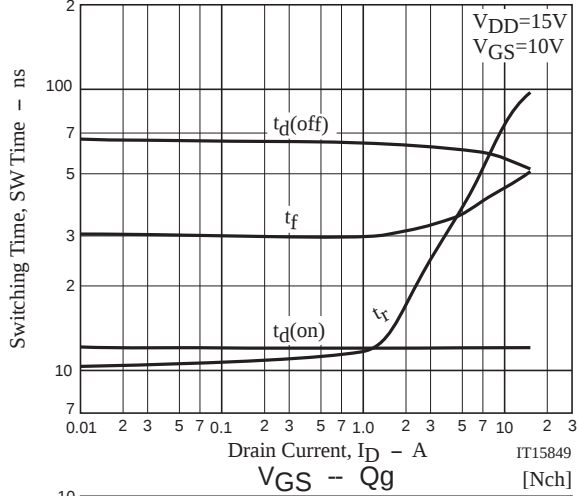
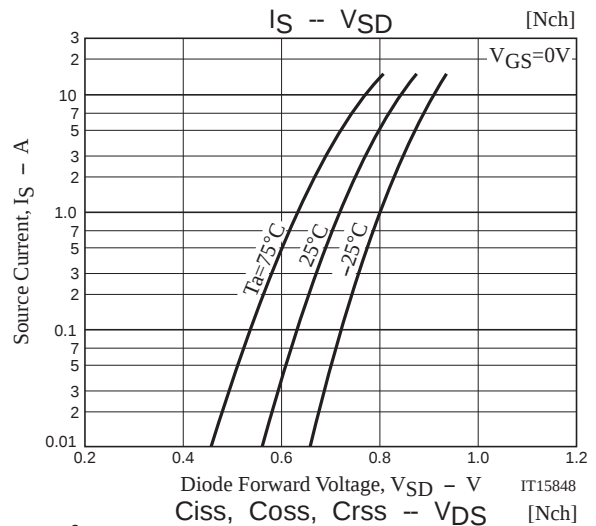
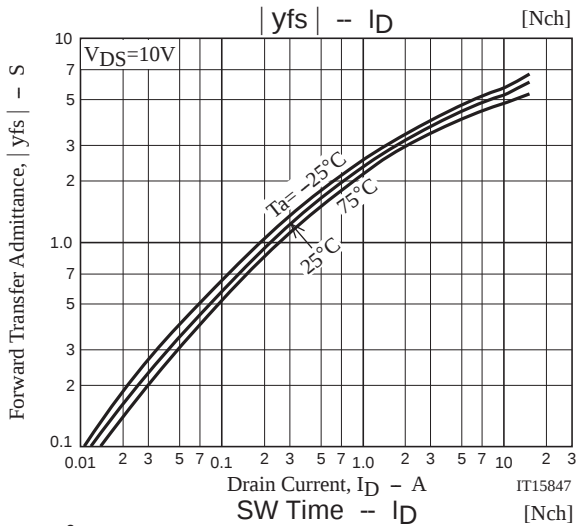
Switching Time Test Circuit

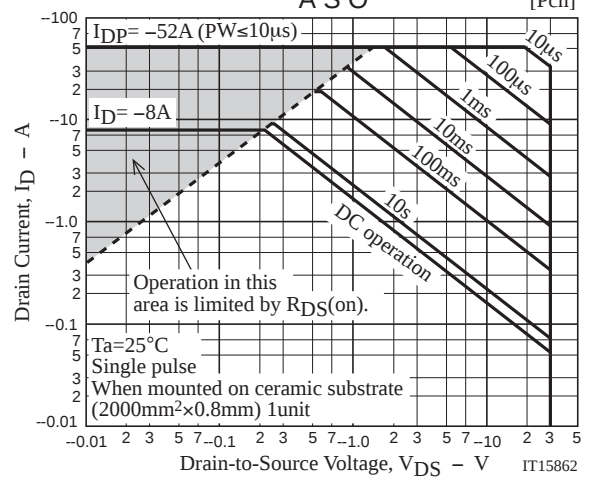
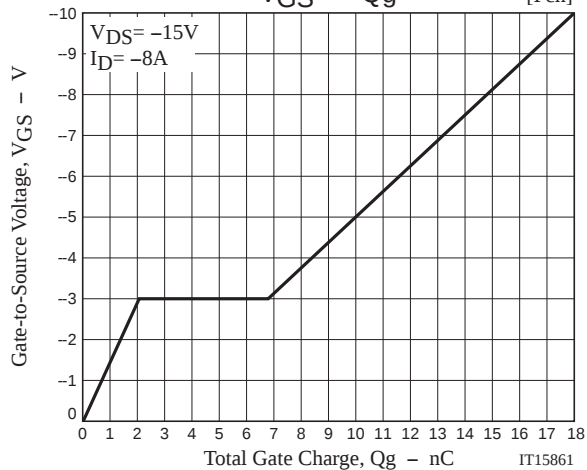
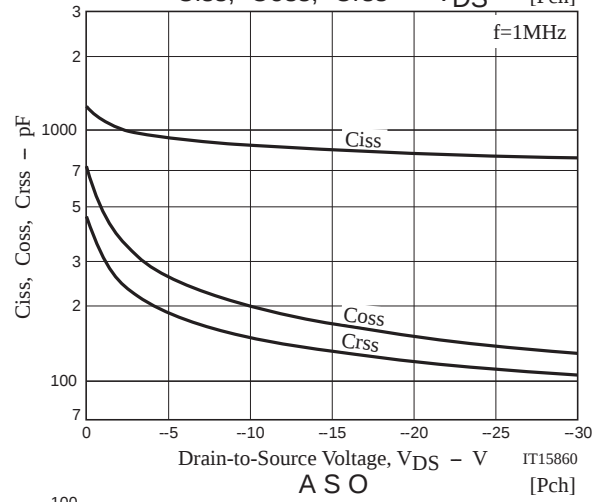
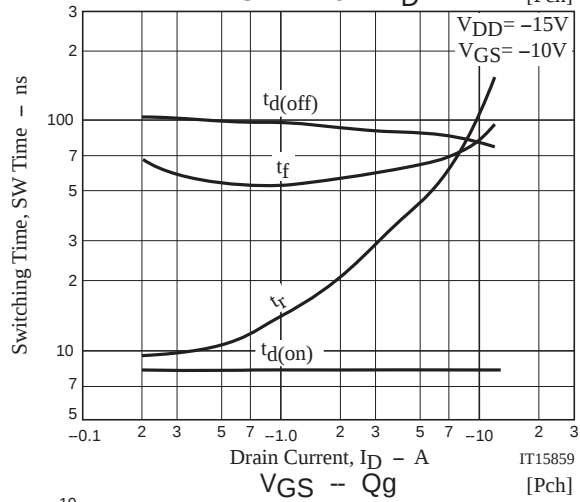
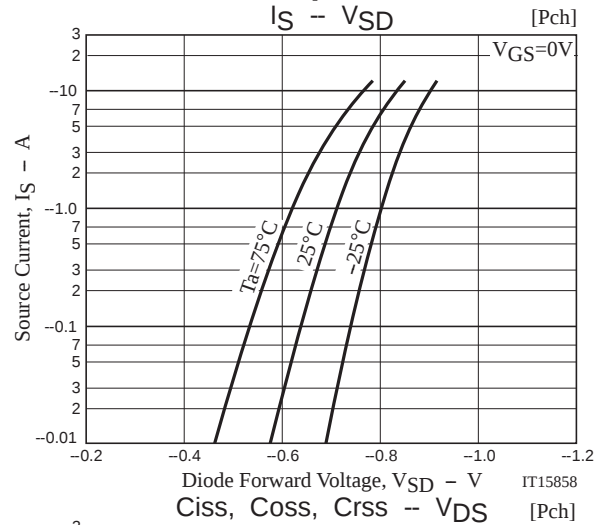
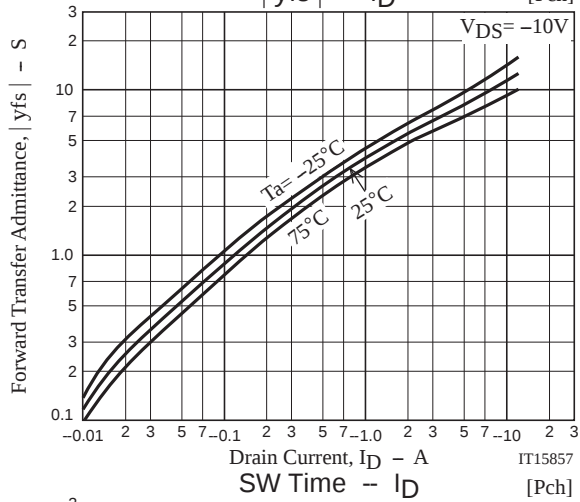
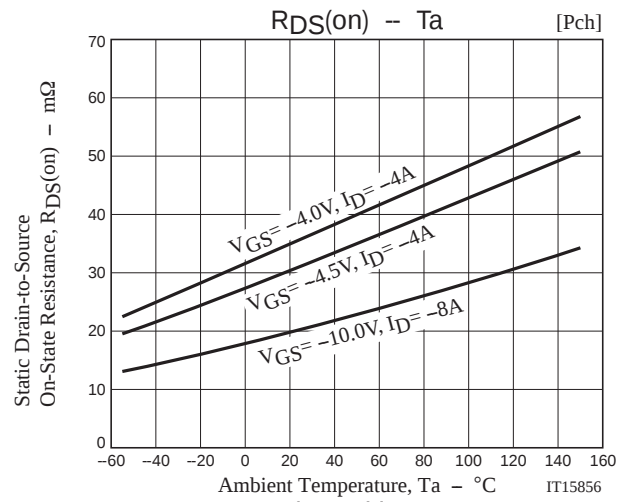
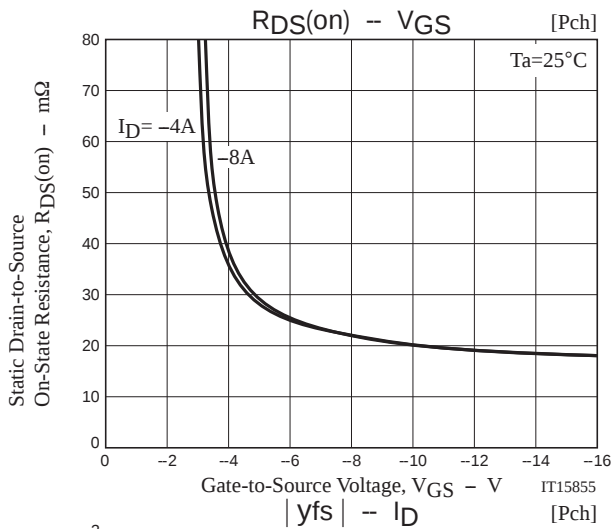
[N-channel]

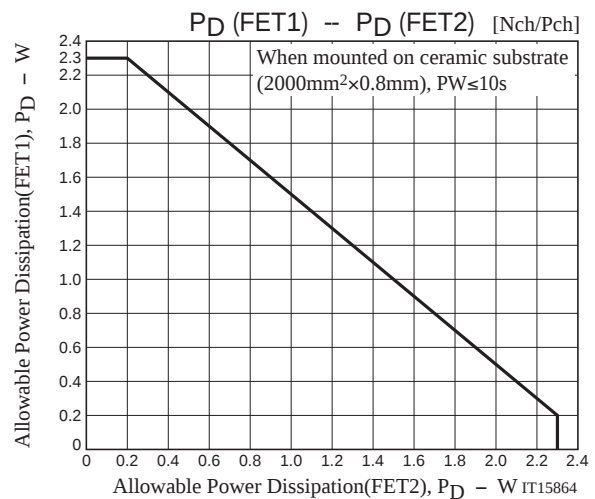
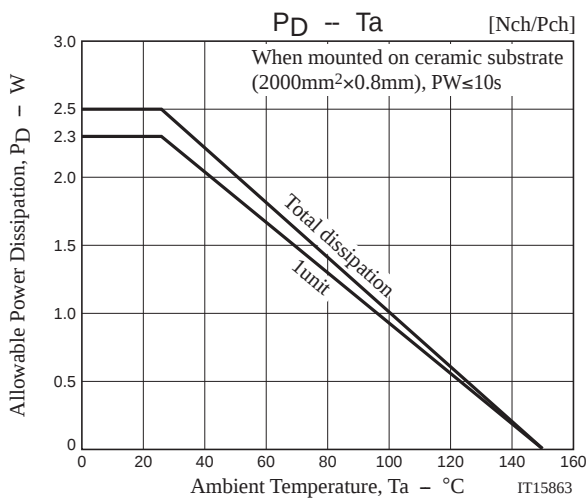


[P-channel]









Note on usage : Since the FW907 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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